



FEATURES

- Ultra Low Loss
- High Ruggedness
- High Short Circuit Capability
- Positive Temperature Coefficient
- With Fast Free-Wheeling Diodes

APPLICATIONS

- Invector
- Converter
- Welder
- SMPS and UPS
- Induction Heating



GD Series Module

ABSOLUTE MAXIMUM RATINGS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit
IGBT				
V_{CES}	Collector - Emitter Voltage		1200	V
V_{GES}	Gate - Emitter Voltage		± 20	V
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}$	210	A
		$T_C=80^{\circ}\text{C}$	150	A
I_{Cpuls}	Pulsed Collector Current	$T_C=25^{\circ}\text{C}, t_p=1\text{ms}$	420	A
		$T_C=80^{\circ}\text{C}, t_p=1\text{ms}$	300	A
P_{tot}	Power Dissipation Per IGBT		1100	W
T_J	Junction Temperature Range		-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range		-40 to +125	$^{\circ}\text{C}$
V_{isol}	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
Free-Wheeling Diode				
V_{RRM}	Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^{\circ}\text{C}$	180	A
		$T_C=80^{\circ}\text{C}$	120	A
$I_{F(RMS)}$	RMS Forward Current		180	A
I_{FSM}	Non-Repetitive Surge Forward Current	$T_J=45^{\circ}\text{C}, t=10\text{ms}, \text{Sine}$	860	A
		$T_J=45^{\circ}\text{C}, t=8.3\text{ms}, \text{Sine}$	900	A

MIMMG150DR120UZA

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
IGBT						
V _{GE(th)}	Gate - Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =6mA	5	6.2	7	V
V _{CE(sat)}	Collector - Emitter Saturation Voltage	I _C =150A, V _{GE} =15V, T _J =25°C		1.8		V
		I _C =150A, V _{GE} =15V, T _J =125°C		2.0		V
I _{CES}	Collector Leakage Current	V _{CE} =1200V, V _{GE} =0V, T _J =25°C		0.4	1	mA
		V _{CE} =1200V, V _{GE} =0V, T _J =125°C		4		mA
I _{GES}	Gate Leakage Current	V _{CE} =0V, V _{GE} =±20V	-200		200	nA
Q _{ge}	Gate Charge	V _{CC} =600V, I _C =150A, V _{GE} =±15V		1550		nC
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f=1MHz		11		nF
C _{oes}	Output Capacitance			0.8		nF
C _{res}	Reverse Transfer Capacitance			0.52		nF
t _{d(on)}	Turn - on Delay Time	V _{CC} =600V, I _C =150A		150		ns
t _r	Rise Time	R _G =7.5 Ω, V _{GE} =±15V		65		ns
t _{d(off)}	Turn - off Delay Time	T _J =25°C		440		ns
t _f	Fall Time	Inductive Load		55		ns
t _{d(on)}	Turn - on Delay Time	V _{CC} =600V, I _C =150A		160		ns
t _r	Rise Time	R _G =7.5 Ω, V _{GE} =±15V		65		ns
t _{d(off)}	Turn - off Delay Time	T _J =125°C		500		ns
t _f	Fall Time	Inductive Load		70		ns
E _{on}	Turn - on Switching Energy	V _{CC} =600V, I _C =150A T _J =25°C		14.9		mJ
		R _G =7.5 Ω T _J =125°C		20.6		mJ
E _{off}	Turn - off Switching Energy	V _{GE} =±15V T _J =25°C		9.8		mJ
		Inductive Load T _J =125°C		15.6		mJ
Free-Wheeling Diode						
V _F	Forward Voltage	I _F =150A, V _{GE} =0V, T _J =25°C		2.0	2.48	V
		I _F =150A, V _{GE} =0V, T _J =125°C		1.7	2.20	V
t _{rr}	Reverse Recovery Time	I _F =150A, V _R =800V		240		ns
I _{RRM}	Max. Reverse Recovery Current	di _F /dt=-1000A/μs		85		A
Q _{rr}	Reverse Recovery Charge	T _J =125°C		10.5		μC

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R _{thJC}	Junction-to-Case Thermal Resistance	Per IGBT			0.11	K /W
R _{thJCD}	Junction-to-Case Thermal Resistance	Per Inverse Diode			0.27	K /W
Torque	Module-to-Sink	Recommended (M6)	3		5	N· m
Torque	Module Electrodes	Recommended (M6)	2.5		5	N· m
Weight				285		g

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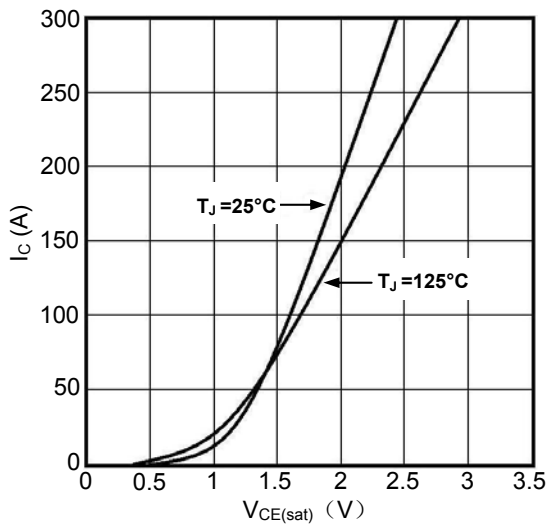


Figure 1. Typical Output characteristics

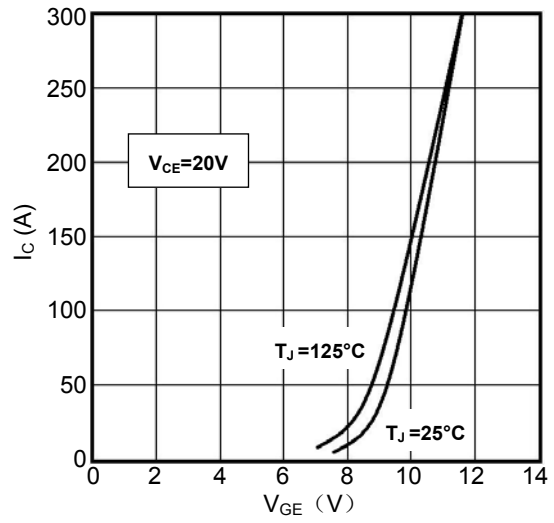


Figure 2. Typical Transfer characteristics

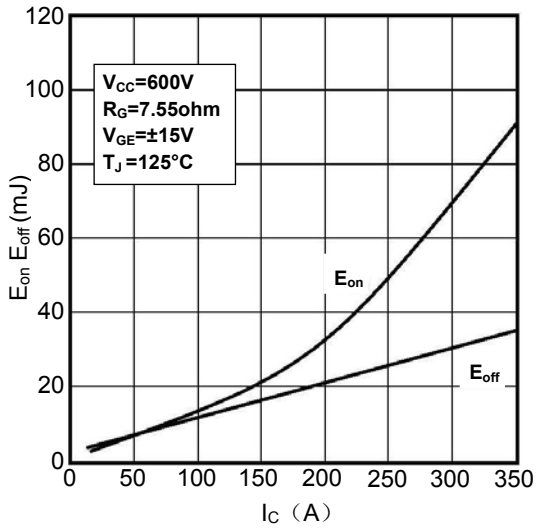


Figure 3. Switching Energy vs. Collector Current

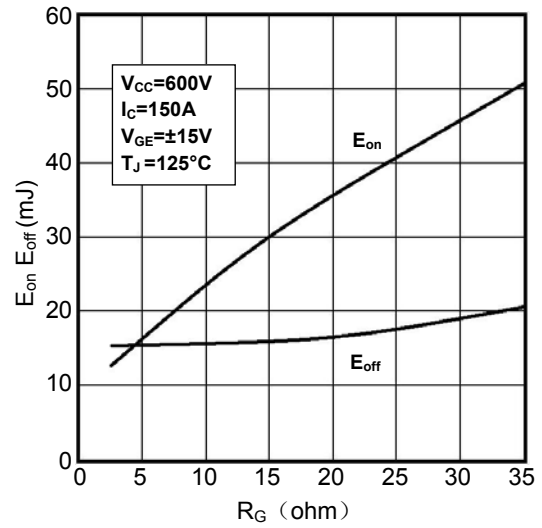


Figure 4. Switching Energy vs. Gate Resistor

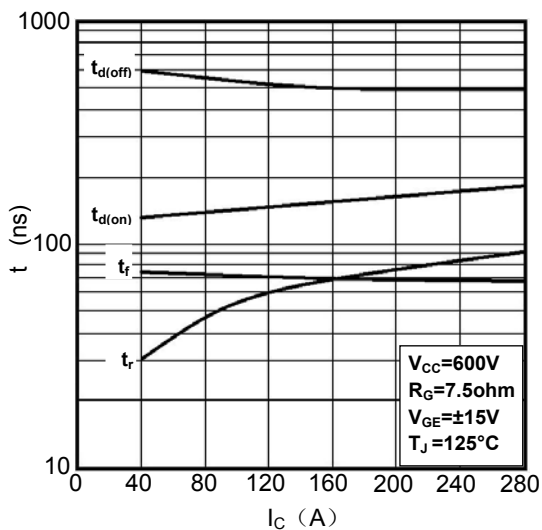


Figure 5. Switching Times vs. Collector Current

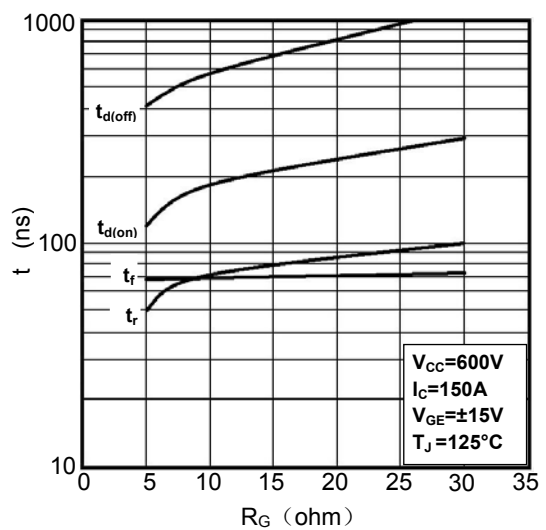


Figure 6. Switching Times vs. Gate Resistor

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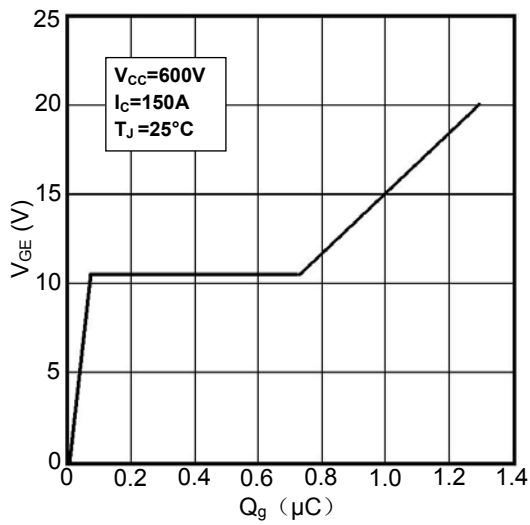


Figure7. Gate Charge characteristics

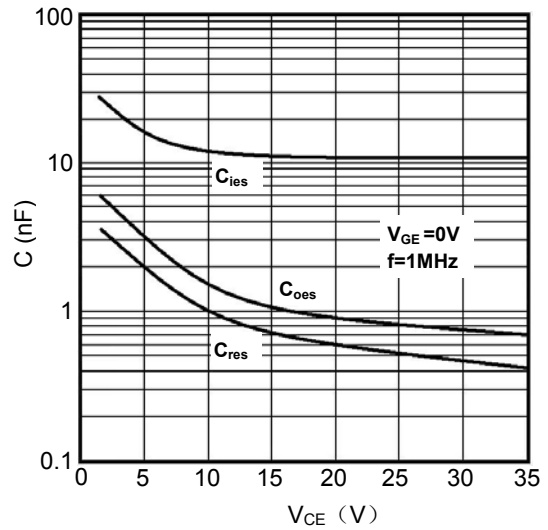


Figure8. Typical Capacitances vs. V_{CE}

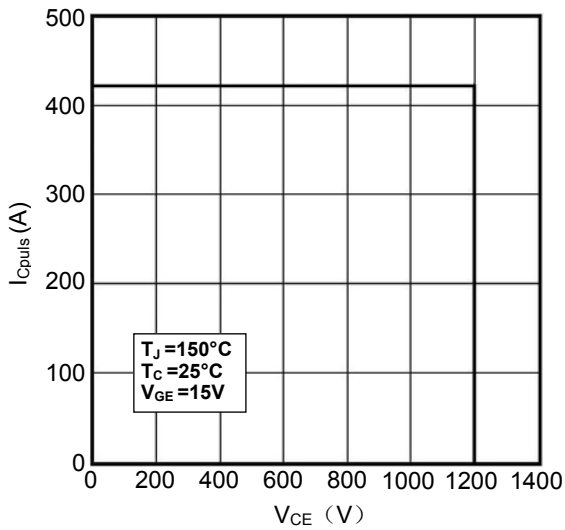


Figure9. Reverse Biased Safe Operating Area

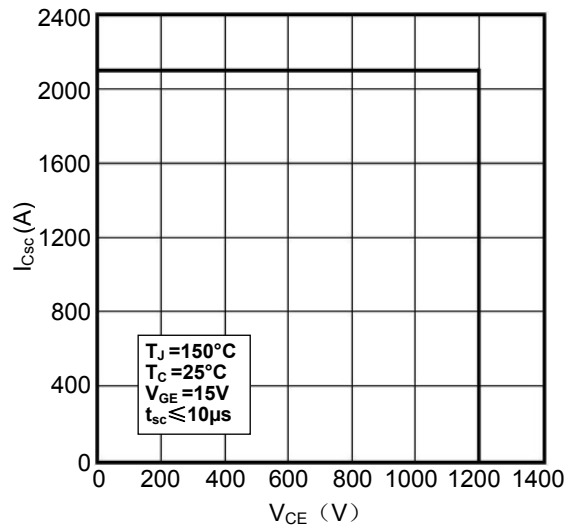


Figure10. Short Circuit Safe Operating Area

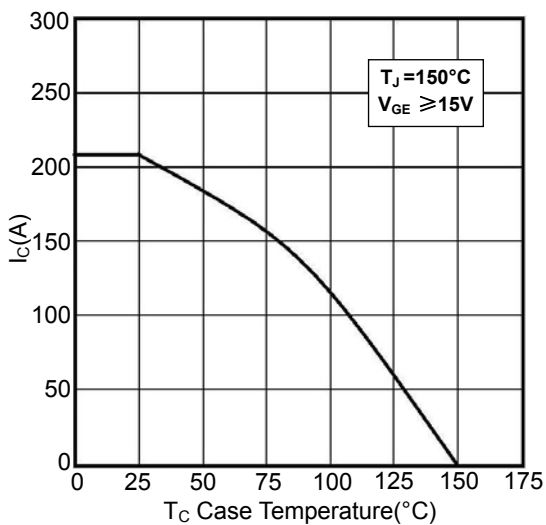


Figure11. Rated Current vs. T_C

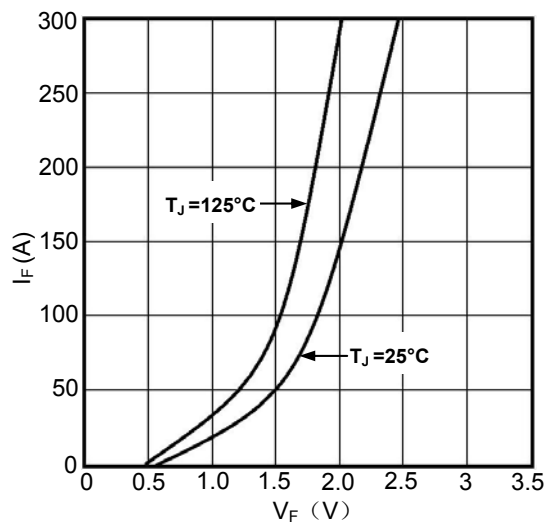


Figure12. Diode Forward Characteristics

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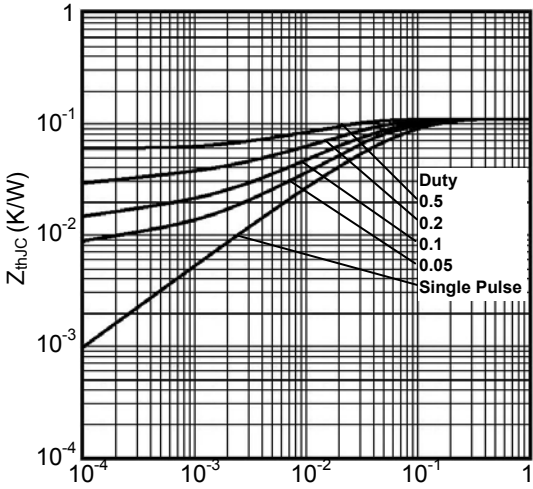


Figure13. Transient Thermal Impedance of IGBT

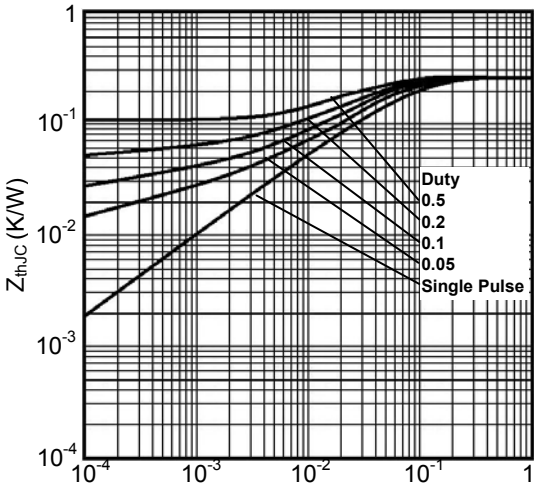


Figure14. Transient Thermal Impedance of Diode

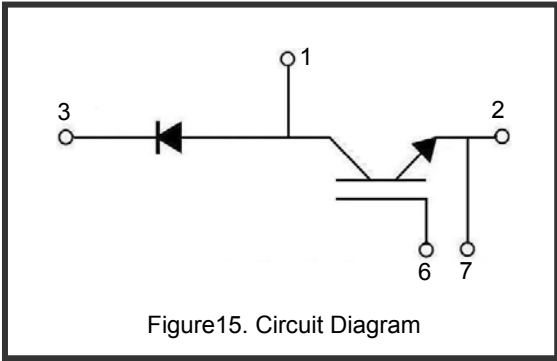
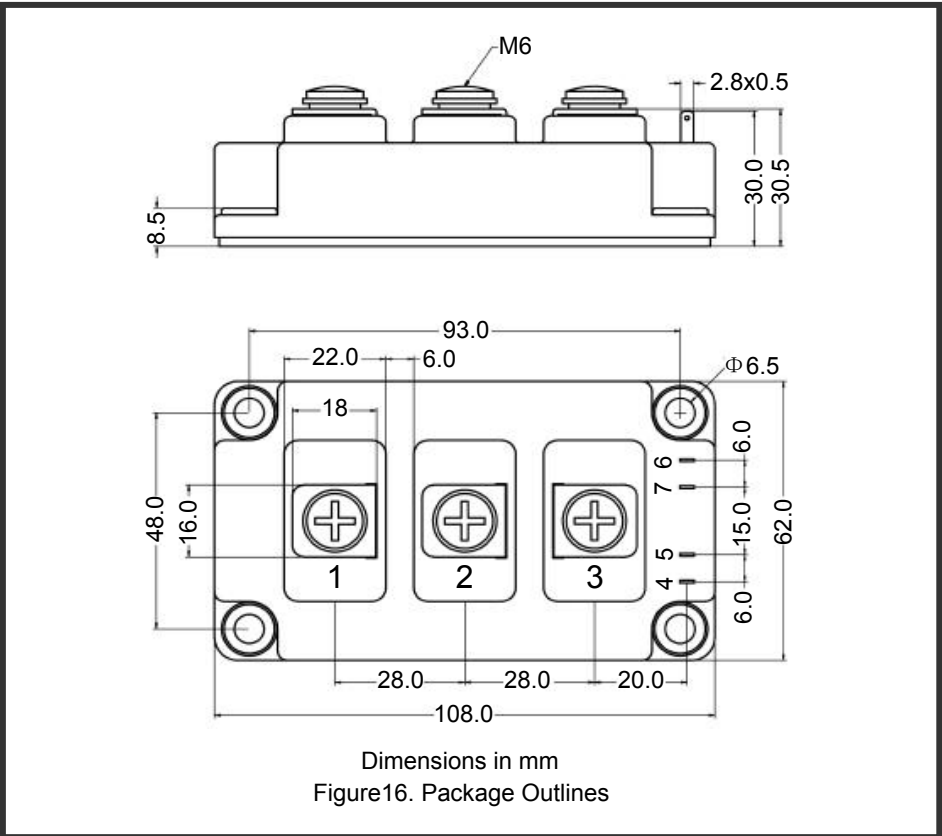


Figure15. Circuit Diagram



Dimensions in mm
Figure16. Package Outlines